

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

BFL4004-

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

• 10V drive

Features

• ON-resistance $R_{DS}(on)=1.9\Omega$ (typ.)

• Input capacitance Ciss=710pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		800	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	6.5	А
	IDpack*2	Tc=25°C (SANYO's ideal heat dissipation condition)*3	4.3	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	13	А
Allowable Power Dissipation	De		2.0	W
	PD	PD Tc=25°C (SANYO's ideal heat dissipation condition)*3	36	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		225	mJ
Avalanche Current *5	IAV		6.5	А

Note :*1 Shows chip capability

*2 Package limited

*3 SANYO's condition is radiation from backside.

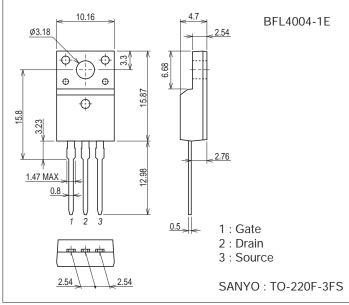
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium. *4 V_{DD} =50V, L=10mH, I_{AV}=6.5A (Fig.1)

*5 L≤10mH, single pulse

Package Dimensions

unit : mm (typ)

7528-001



Product & Package Information

• Package :	TO-220F-3FS
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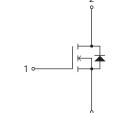
• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./tube

Marking

Electrical Connection





SANYO Semiconductor Co., Ltd. http://www.sanyosemi.com/en/network/

Electrical Characteristics at Ta=25°C	acteristics at Ta=25°C
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Parameter	Symbol	Conditions		Ratings			
Parameter	Symbol	Conditions	min typ		max	unit Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	800			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =640V, V _{GS} =0V			1.0	mA	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	$\begin{array}{c c c c c c c c c c c c c c c c c c c $		4.0	V	
Forward Transfer Admittance	yfs	VDS=20V, ID=3.25A	In the second se			S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=3.25A, VGS=10V		1.9	2.5	Ω	
Input Capacitance	Ciss			710		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		120		pF	
Reverse Transfer Capacitance	Crss			42		pF	
Turn-ON Delay Time	t _d (on)			17		ns	
Rise Time	tr			44		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		130		ns	
Fall Time	tf	-		44		ns	
Total Gate Charge	Qg			36		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		6.2		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		18		nC	
Diode Forward Voltage	V _{SD}	IS=6.5A, VGS=0V 0.85		1.2	V		
Reverse Recovery Time	t _{rr}	See Fig.3		970		ns	
Reverse Recovery Charge	Q _{rr}	IS=6.5A, VGS=0V, di/dt=100A/µs		6700		nC	

Fig.1 Unclamped Inductive Switching Test Circuit

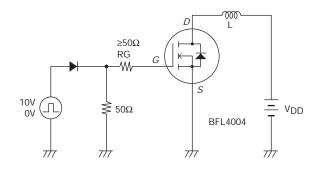
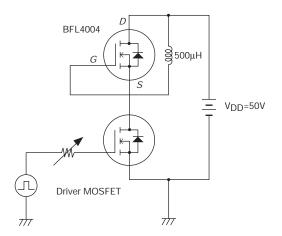


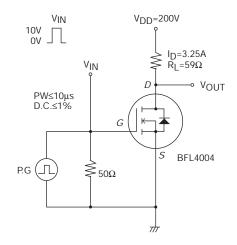
Fig.3 Reverse Recovery Time Test Circuit



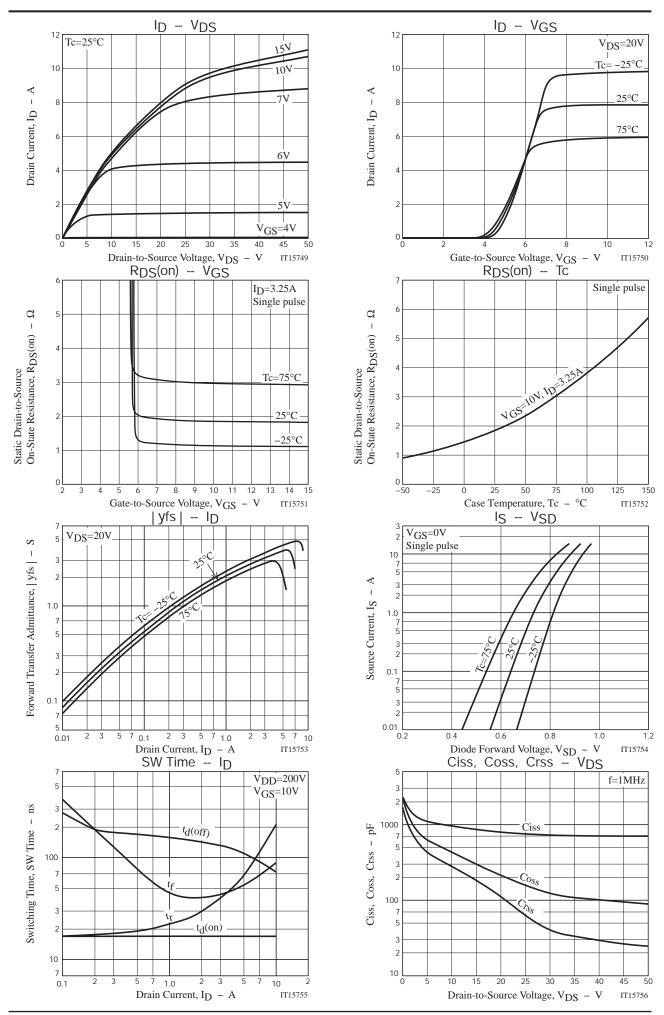
Ordering Information

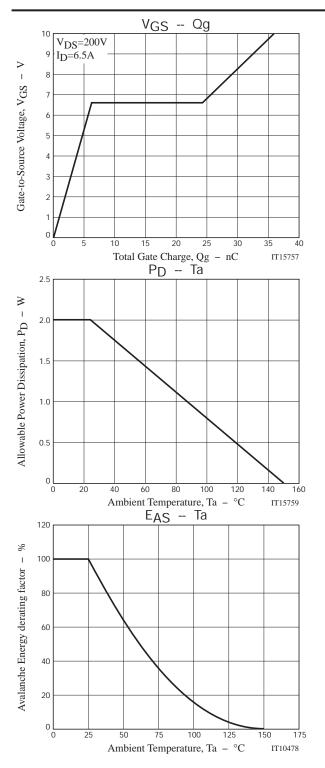
Device	Package	Shipping	memo
BFL4004-1E	TO-220F-3FS	50pcs./tube	Pb Free

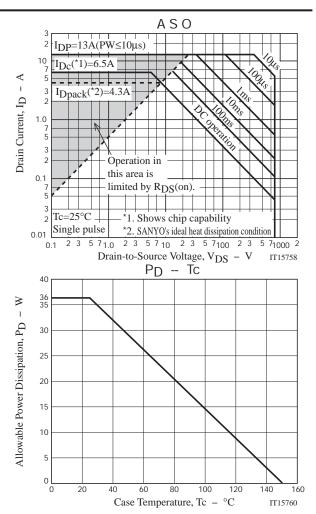
Fig.2 Switching Time Test Circuit



BFL4004







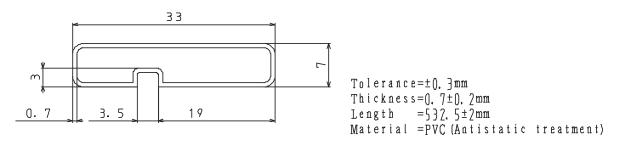
Magazine Specification BFL4004-1E

1. Packing Format

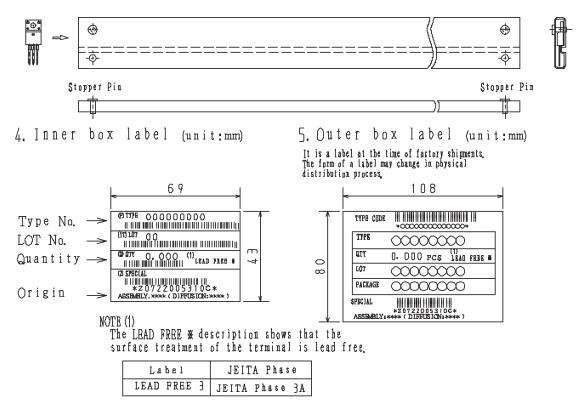
Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format	
Turninger Humit	IIIa6 ab tare Itanis		Inner box	Quter dax	Inner BOX	Outer BOX
TO-220F-3F\$	TO-220F	50	1,000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm {external} 590×225×178

2. Magazine dimensions

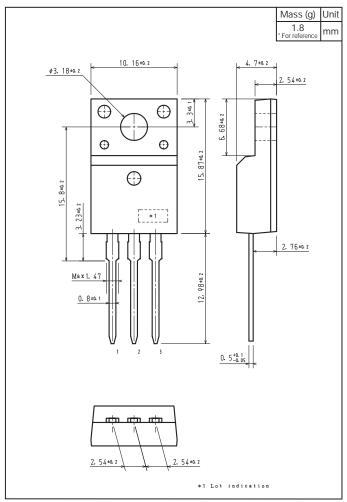
(unit:mm)



3. Storage method to magazine



Outline Drawing BFL4004-1E



Note on usage : Since the BFL4004 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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